

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

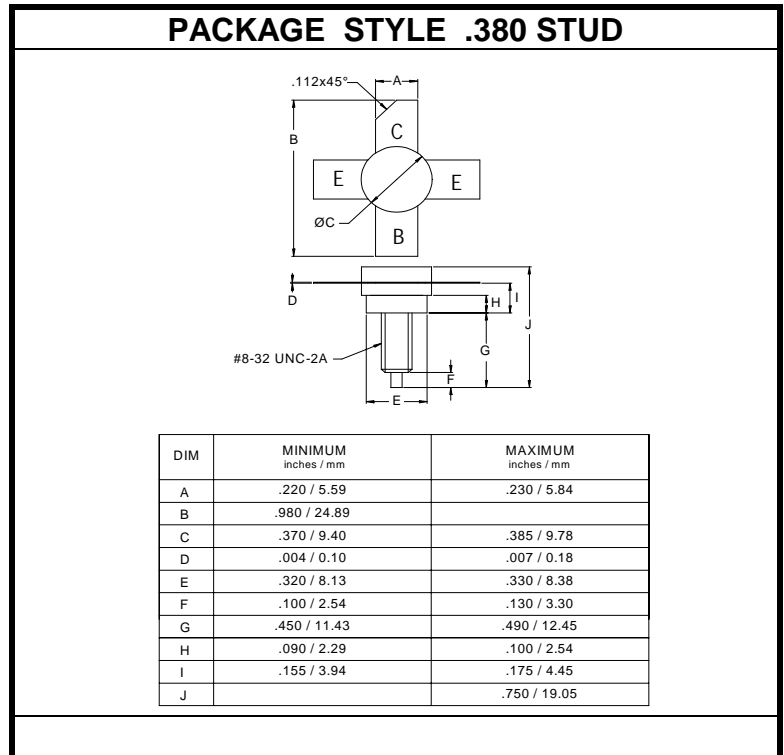
The **ASI BLX39** is Designed for broadband amplifier operations up to 175 MHz.

FEATURES:

- $P_G = 7.6$ dB min. at 40 W/175 MHz
- Emitter Resistors Ballasted
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	5.0 A
V_{CB}	65 V
V_{CE}	35 V
P_{DISS}	60 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.9 °C/W


CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	35			V
BV_{CES}	$I_C = 200$ mA	65			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CES}	$V_E = 28$ V			5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	10		100	---
C_{ob}	$V_{CB} = 28$ V $f = 1.0$ MHz			65	pF
P_G	$V_{CE} = 28$ V $P_{IN} = 7.0$ W $f = 175$ MHz	7.6			dB
η_C		60			%